

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended)      A method for the cleaning of an integrated circuit substrate, comprising:

contacting the integrated circuit substrate with ~~an aqueous composition comprising an effective amount~~ a combination of (a) hydrogen fluoride, followed by (b) a mixture of hydrogen peroxide with a compound selected from the group consisting of ammonium hydroxide, hydrochloric acid and sulfuric acid, wherein ~~by products of a high-k dielectric dry etch process are removed from the integrated circuit substrate~~ said cleaning further comprises contacting the integrated circuit substrate with the combination at a temperature from about 15° C to about 90° C.

2. (currently amended)      The method as recited in claim 1, wherein the aqueous ~~composition~~ combination comprises from about 0.05 to about 30 percent of hydrogen fluoride based on the volume of the ~~composition~~ combination.

3. (currently amended)      The method as recited in claim 1, wherein the aqueous ~~composition~~ combination comprises from about 0.05 to about 30 percent of ammonium hydroxide based on the volume of the ~~composition~~ combination.

4. (currently amended)      The method as recited in claim 1, wherein the aqueous ~~composition~~ combination comprises from about 0.05 to about 30 percent of hydrogen peroxide based on the volume of the ~~composition~~ combination.

5. (canceled)

6. (currently amended) The method as recited in claim 1, wherein said cleaning comprises contacting the integrated circuit substrate with the ~~aqueous cleaning composition~~ combination from about 10 seconds to about 10 minutes.

7. (original) The method as recited in claim 1, wherein said cleaning further comprises megasonic physical cleaning.

8-18. (canceled)